

**REMARKS**

Claims 1-40 are canceled, leaving claims 41-47 pending in the application.

Applicant requests substantive examination of pending claims 41-47

Respectfully submitted,

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By: 

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

.priority Application Serial No. .... 09/633,556  
. priority Filing Date ..... August 7, 2000  
Inventor ..... Gurtej S. Sandhu et al.  
Assignee ..... Micron Technology, Inc.  
priority Group Art Unit ..... 2813  
priority Examiner ..... Laura M. Schillinger  
Attorney's Docket No. ..... MI22-1898  
Title: Transistor Structures

**VERSION WITH MARKINGS TO SHOW CHANGES MADE**  
**ACCOMPANYING PRELIMINARY AMENDMENT**

**In the Specification**

The replacement specification paragraphs incorporate the following amendments. Underlines indicate insertions and ~~strikeouts~~ indicate deletions.

The title is amended as follows: Transistor Structures, ~~Methods of Incorporating Nitrogen into Silicon-Oxide-Containing Layers, and Methods of Forming Transistors~~

The following is inserted on p. 1 before the "Technical Field" section,

**CROSS REFERENCE TO RELATED APPLICATION**

This patent resulted from a divisional application of U.S. Patent Application Serial No. 09/633,556, which was filed on August 7, 2000.